

Silicon PNP Power Transistors

2SA1078

DESCRIPTION

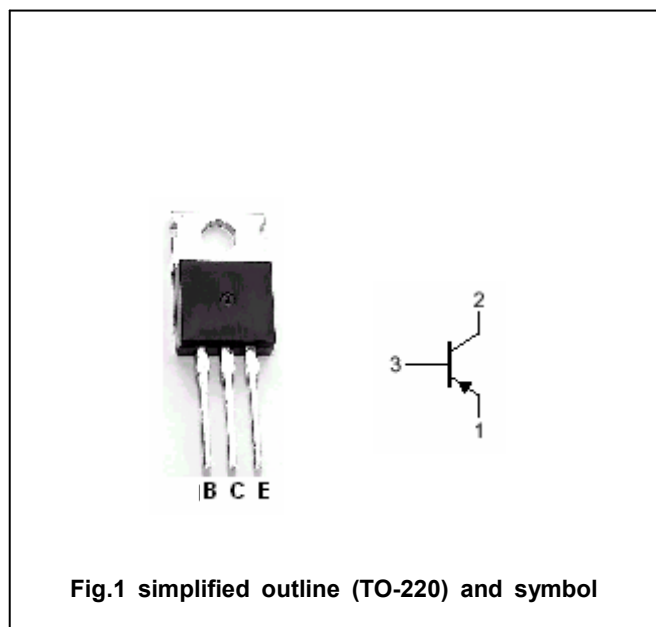
- With TO-220 package
- Complement to type 2SC2528
- High transition frequency
- Excellent safe operating area

APPLICATIONS

- High-frequency power amplifier
- Audio power amplifiers and drivers

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-120	V
V_{CEO}	Collector-emitter voltage	Open base	-120	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-2	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	25	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-65~150	$^\circ\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-1mA, R_{BE}=\infty$	-120			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=-1\mu A, I_E=0$	-120			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=-1\mu A, I_C=0$	-5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-0.7A; I_B=-70mA$		-0.45	-1.0	V
V_{BE}	Base-emitter on voltage	$I_C=-0.7A; V_{CE}=-5V$		-0.8	-1.7	V
I_{CBO}	Collector cut-off current	$V_{CB}=-120V; I_E=0$			-1	μA
I_{CEO}	Collector cut-off current	$V_{CE}=-120V; I_B=0$			-100	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-5V; I_C=0$			-1	μA
h_{FE-1}	DC current gain	$I_C=-0.3A; V_{CE}=-5V$	60		350	
h_{FE-2}	DC current gain	$I_C=-0.7A; V_{CE}=-5V$	50			
f_T	Transition frequency	$I_C=-0.5A; V_{CE}=-10V; f=10MHz$		140		MHz
C_{OB}	Output capacitance	$I_E=0; V_{CB}=-20V; f=1MHz$		100		pF

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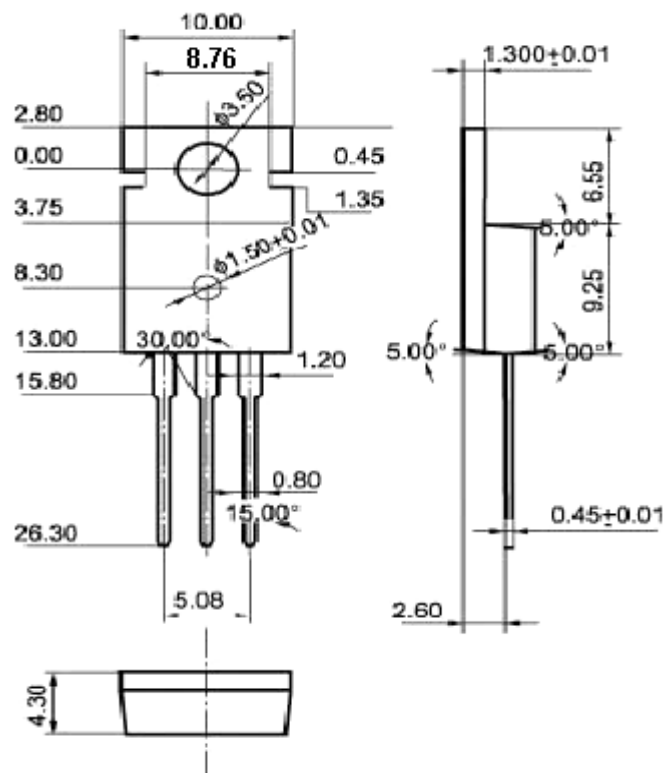


Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)